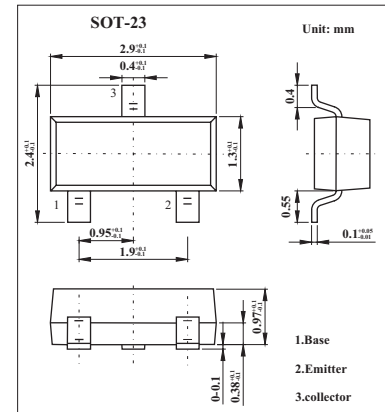


PNP Transistor KST9012

■ Features

- Excellent hFE linearity
- Collector Current : $I_c = -0.5A$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-25	V
Emitter - Base Voltage	V_{EBO}	-5	V
Collector Current to Continuous	I_c	-500	mA
Collector Power Dissipation	P_c	300	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector - base breakdown voltage	V_{CBO}	$I_c = -100\mu A, I_E = 0$	-40			V
Collector - emitter breakdown voltage	V_{CEO}	$I_c = -1 mA, I_B = 0$	-25			V
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100\mu A, I_c = 0$	-5			V
Collector cut - off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut - off current	I_{CEO}	$V_{CB} = -20V, I_E = 0$			-0.1	μA
Emitter cut - off current	I_{EBO}	$V_{EB} = -5V, I_c = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_c = -50mA$	120		400	
Collector - emitter saturation voltage	$V_{CE(sat)}$	$I_c = -500 mA, I_B = -50mA$			-0.6	V
Base - emitter voltage	$V_{BE(sat)}$	$I_c = -500 mA, I_B = -50mA$			-1.2	V
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			5	pF
Transition frequency	f_T	$V_{CE} = -6V, I_c = -20mA, f = 30MHz$	150			MHz

■ hFE Classification

Marking	2T1		
Rank	L	H	J
hFE	120~200	200~350	300~400

KST9012

■ Typical Characteristics

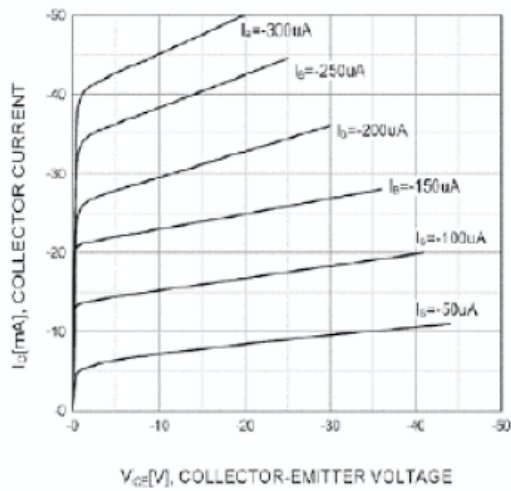


Fig.1 Static Characteristic

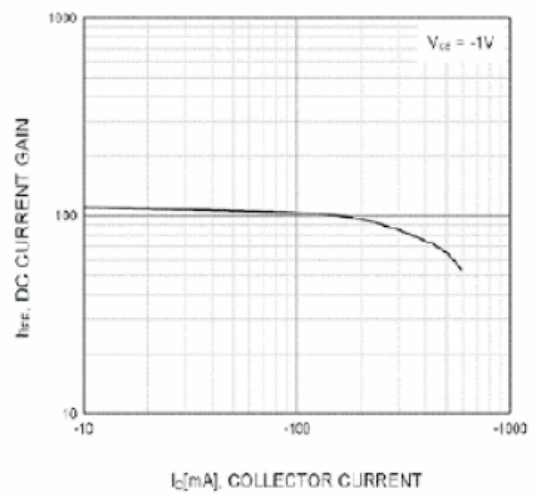


Fig.2 DC Current Gain

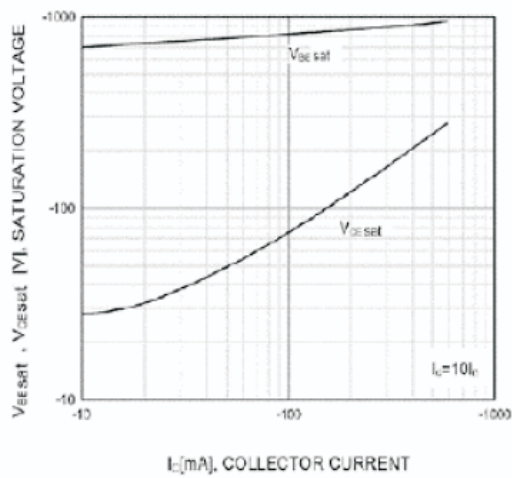


Fig.3 Base-Emitter Saturation Voltage
Collector- Emitter Saturation Voltage

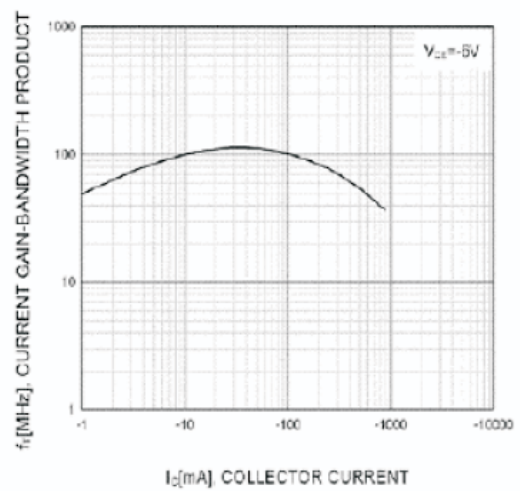


Fig.4 Current Gain Bandwidth Product